

Journal of ELECTRONIC MATERIALS

Volume 39, No. 6

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June 2010

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ABSTRACTING/INDEXING: JEM is abstracted or indexed in *Applied Science & Technology Index, Applied Science & Technology Abstracts, Bureau Bibliographique International, Chemical Abstracts, Chemical Abstracts Service, Chemical Titles, Current Contents, Electronics and Communications Abstracts Journal, Engineering Index, Referativnyi Zhurnal, Science Citation Index, and Solid State Abstracts Journal.*

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